## NOTES:

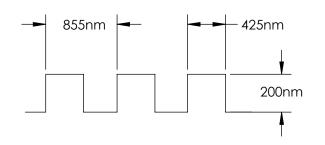
- SUBSTRATE MATERIAL: Single Crystal Silicon
- PERIOD: 855 ±42.75nm
   LINE WIDTH: 425 ±42.5nm
   GROOVE DEPTH: 200 ±30nm

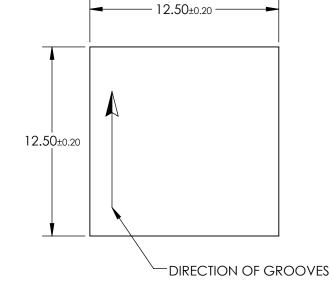


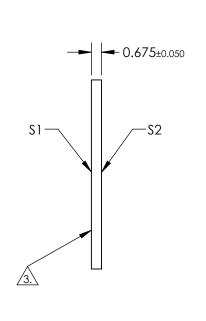
RIE TREATED SURFACE

4. Rohs Compliant









## FOR INFORMATION ONLY: DO NOT MANUFACTURE PARTS TO THIS DRAWING

SPECIFICATIONS SUBJECT TO CHANGE WITHOUT NOTICE DIMENSIONS ARE FOR REFERENCE ONLY

	\$1	\$2		
SHAPE	PLANO	PLANO		
SURFACE QUALITY	60-40 (within CA)	FINE GRIND		
CLEAR APERTURE	11.50 x 11.50	N/A		
BEVEL	PROTECTED AS NEEDED	PROTECTED AS NEEDED		

THIRD ANGLE PROJECTION	$\phi \Leftrightarrow$	TITLE
ALL DIMS IN	mm	DWC

B	<b>Edmund Optics</b> ®
TLE	II-VI LightSmyth™ 855nm, 200nm Groove Depth 12 5mm Sq. Linear Silicon Nanostamp

l DIMS IN	mm	DWG NO	16855	SHEET 1 OF 1